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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/796,427	03/09/2004	Mou-Shiung Lin	MEG03-005	1870
7590 STEPHEN B. ACKERMAN 28 DAVIS AVENUE POUGHKEEPSIE, NY 12603			EXAMINER LEWIS, MONICA	
		ART UNIT 2822	PAPER NUMBER	
SHORTENED STATUTORY PERIOD OF RESPONSE	MAIL DATE	DELIVERY MODE		
3 MONTHS	02/12/2007	PAPER		

Please find below and/or attached an Office communication concerning this application or proceeding.

If NO period for reply is specified above, the maximum statutory period will apply and will expire 6 MONTHS from the mailing date of this communication.

<b>Office Action Summary</b>	<b>Application No.</b>	<b>Applicant(s)</b>	
	10/796,427	LIN ET AL.	
	Examiner Monica Lewis	Art Unit 2822	

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

#### Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) OR THIRTY (30) DAYS, WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

#### Status

1) Responsive to communication(s) filed on 20 November 2006.  
 2a) This action is FINAL.                    2b) This action is non-final.  
 3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

#### Disposition of Claims

4) Claim(s) 69-90 is/are pending in the application.  
 4a) Of the above claim(s) \_\_\_\_\_ is/are withdrawn from consideration.  
 5) Claim(s) \_\_\_\_\_ is/are allowed.  
 6) Claim(s) 69-90 is/are rejected.  
 7) Claim(s) \_\_\_\_\_ is/are objected to.  
 8) Claim(s) \_\_\_\_\_ are subject to restriction and/or election requirement.

#### Application Papers

9) The specification is objected to by the Examiner.  
 10) The drawing(s) filed on 09 March 2004 is/are: a) accepted or b) objected to by the Examiner.  
     Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).  
     Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).  
 11) The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

#### Priority under 35 U.S.C. § 119

12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).  
 a) All    b) Some \* c) None of:  
 1. Certified copies of the priority documents have been received.  
 2. Certified copies of the priority documents have been received in Application No. \_\_\_\_\_.  
 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

\* See the attached detailed Office action for a list of the certified copies not received.

#### Attachment(s)

1) <input type="checkbox"/> Notice of References Cited (PTO-892)	4) <input type="checkbox"/> Interview Summary (PTO-413)
2) <input type="checkbox"/> Notice of Draftsperson's Patent Drawing Review (PTO-948)	Paper No(s)/Mail Date. _____
3) <input type="checkbox"/> Information Disclosure Statement(s) (PTO/SB/08) Paper No(s)/Mail Date _____	5) <input type="checkbox"/> Notice of Informal Patent Application
	6) <input type="checkbox"/> Other: _____

## **DETAILED ACTION**

1. This office action is in response to the amendment filed November 20, 2006.

### ***Claim Rejections - 35 USC § 103***

2. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

3. Claims 69-74 and 80-85 are rejected under 35 U.S.C. 103(a) as being unpatentable over Akram (U.S. Patent No. 6,544,880) in view of Yanagida (U.S. Patent No. 6,545,355).

In regards to claim 69, Akram discloses the following:

- a) a semiconductor substrate (11) (For Example: See Figure 1);
- b) multiple transistors in or on said semiconductor substrate (For Example: See Figure 1);
- c) an interconnecting metallization structure (12') over said semiconductor substrate (For Example: See Figure 2F);
- d) a passivation layer (13) over said interconnecting metallization structure, wherein an opening in said passivation layer exposes a contact point of said interconnecting metallization structure (For Example: See Figure 2F);
- e) a first metal layer (12'') over said contact point (For Example: See Figure 2F and Column 5 Lines 45-50); and
- f) a second metal layer (12'') over said first metal layer, wherein said second metal layer is used to be wire bonded (For Example: See Figure 2F).

In regards to claim 69, Akram fails to disclose the following:

- a) a first metal layer comprises aluminum.

However, Yanagida discloses a first metal layer (20a) that comprises aluminum (For Example: See Figure 1). It would have been obvious to one having ordinary skill in the art at the time the invention was made to modify the semiconductor of Akram to include aluminum as disclosed in Yanagida because it aids in providing high durability (For Example: See Column 3 Lines 5-7).

Additionally, since Akram and Yanagida are both from the same field of endeavor, the purpose disclosed by Yanagida would have been recognized in the pertinent art of Akram.

In regards to claims 70 and 81, Akram discloses the following:

a) passivation layer comprises a topmost nitride layer of said semiconductor chip or wafer (For Example: See Column 5 Lines 35 and 36).

In regards to claims 71 and 82, Akram discloses the following:

a) passivation layer comprises a topmost oxide layer of said semiconductor chip or wafer (For Example: See Column 5 Lines 35 and 36).

In regards to claims 72 and 83, Akram discloses the following:

a) interconnecting metallization structure comprises copper (For Example: See Column 5 Line 6).

In regards to claims 73 and 84, Akram discloses the following:

a) second metal layer comprises gold (For Example: See Column 5 Line 19).

In regards to claims 74 and 85, Akram discloses the following:

a) second metal layer comprises copper (For Example: See Column 4 Lines 29-32).

In regards to claim 80, Akram discloses the following:

a) a semiconductor substrate (For Example: See Figure 1);

b) multiple transistors in or on said semiconductor substrate (For Example: See Figure 1);

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- c) an interconnecting metallization structure over said semiconductor substrate (For Example: See Figure 2F);
- d) a passivation layer over said interconnecting metallization structure, wherein an opening in said passivation layer exposes a contact point of said interconnecting metallization structure (For Example: See Figure 2F);
- e) a first metal layer over said contact point (For Example: See Figure 2F and Column 5 Lines 45-50);
- f) a second metal layer over said first metal layer (For Example: See Figure 2F); and
- g) a wire wirebonded over said second metal layer (For Example: See Figure 2F).

In regards to claim 80, Akram fails to disclose the following:

- a) a first metal layer comprises aluminum.

However, Yanagida discloses a first metal layer (20a) that comprises aluminum (For Example: See Figure 1). It would have been obvious to one having ordinary skill in the art at the time the invention was made to modify the semiconductor of Akram to include aluminum as disclosed in Yanagida because it aids in providing high durability (For Example: See Column 3 Lines 5-7).

Additionally, since Akram and Yanagida are both from the same field of endeavor, the purpose disclosed by Yanagida would have been recognized in the pertinent art of Akram.

4. Claims 75 and 86 are rejected under 35 U.S.C. 103(a) as being unpatentable over Akram (U.S. Patent No. 6,544,880) in view of Yanagida (U.S. Patent No. 6,545,355) and Galloway (U.S. Patent No. 5,783,868).

In regards to claims 75 and 86, Akram fails to disclose the following:

- a) second metal layer has a thickness of between about 2um and 20um.

However, Galloway discloses a semiconductor device that has a gold layer that has a thickness of between about 2um and 20um (For Example: See Column 3 Lines 41-43). It would have been obvious to one having ordinary skill in the art at the time the invention was made to modify the semiconductor of Akram to include a gold layer that has a thickness of between about 2um and 20um as disclosed in Galloway because it aids in avoiding damage to the contact area (For Example: See Column 1 Lines 33-67 and Column 2 Lines 1-10).

Additionally, since Akram and Galloway are both from the same field of endeavor, the purpose disclosed by Galloway would have been recognized in the pertinent art of Akram.

Finally, the applicant has not established the critical nature of a “second metal layer has a thickness of between about 2um and 20um.” “The law is replete with cases in which the difference between the claimed invention and the prior art is some range or other variable within the claims. . . . In such a situation, the applicant must show that the particular range is critical, generally by showing that the claimed range achieves unexpected results relative to the prior art range.” *In re Woodruff*, 919 F.2d 1575, 16 USPQ2d 1934 (Fed. Cir. 1990). Therefore, it would have been obvious to one having ordinary skill in the art at the time the invention was made to have various ranges.

5. Claims 76-78 and 87-89 are rejected under 35 U.S.C. 103(a) as being unpatentable over Akram (U.S. Patent No. 6,544,880) in view of Yanagida (U.S. Patent No. 6,545,355) and Weng (U.S. Patent No. 6,720,243).

In regards to claims 76 and 87, Akram fails to disclose the following:

a) a third metal layer between said first and second layers, wherein said third metal layer comprises a titanium-tungsten alloy.

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However, Weng discloses a semiconductor device that has a third metal layer (208) between said first (206) and second layers (210), wherein said third metal layer comprises a titanium-tungsten alloy (For Example: See Column 3 Lines 30-35). It would have been obvious to one having ordinary skill in the art at the time the invention was made to modify the semiconductor of Akram to include a third metal layer between said first and second layers, wherein said third metal layer comprises a titanium-tungsten alloy as disclosed in Weng because it aids in providing good bump quality (For Example: See Column 2 Lines 25-65).

Additionally, since Akram and Weng are both from the same field of endeavor, the purpose disclosed by Weng would have been recognized in the pertinent art of Akram.

In regards to claims 77 and 88, Akram fails to disclose the following:

a) a third metal layer between said first and second layers, wherein said third metal layer comprises chromium.

However, Weng discloses a semiconductor device that has a third metal layer (208) between said first (206) and second layers (210), wherein said third metal layer comprises chromium (For Example: See Column 3 Lines 30-35). It would have been obvious to one having ordinary skill in the art at the time the invention was made to modify the semiconductor of Akram to include a third metal layer between said first and second layers, wherein said third metal layer comprises chromium as disclosed in Weng because it aids in providing good bump quality (For Example: See Column 2 Lines 25-65).

Additionally, since Akram and Weng are both from the same field of endeavor, the purpose disclosed by Weng would have been recognized in the pertinent art of Akram.

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In regards to claims 78 and 89, Akram fails to disclose the following:

a) a third metal layer between said first and second layers, wherein said third metal layer comprises titanium.

However, Weng discloses a semiconductor device that has a third metal layer (208) between said first (206) and second layers (210), wherein said third metal layer comprises titanium (For Example: See Column 3 Lines 30-35). It would have been obvious to one having ordinary skill in the art at the time the invention was made to modify the semiconductor of Akram to include a third metal layer between said first and second layers, wherein said third metal layer comprises titanium as disclosed in Weng because it aids in providing good bump quality (For Example: See Column 2 Lines 25-65).

Additionally, since Akram and Weng are both from the same field of endeavor, the purpose disclosed by Weng would have been recognized in the pertinent art of Akram.

6. Claims 79 and 90 are rejected under 35 U.S.C. 103(a) as being unpatentable over Akram (U.S. Patent No. 6,544,880) in view of Yanagida (U.S. Patent No. 6,545,355) and Chikawa et al. (U.S. Patent No. 5,310,699).

In regards to claims 79 and 90, Akram fails to disclose the following:

a) a third metal layer between said first and second layers, wherein said third metal layer has a thickness of between 2700 and 3300 Angstroms.

However, Chikawa et al. ("Chikawa") discloses a semiconductor device that has a titanium-tungsten layer that has a thickness of between 2700 and 3300 Angstroms (For Example: See Column 4 Lines 22-25). It would have been obvious to one having ordinary skill in the art at the time the invention was made to modify the semiconductor of Akram to include a titanium-

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tungsten layer that has a thickness of between 2700 and 3300 Angstroms as disclosed in Chikawa because it aids in providing good adhesion (For Example: See Column 4 Lines 22-25).

Additionally, since Akram and Chikawa are both from the same field of endeavor, the purpose disclosed by Chikawa would have been recognized in the pertinent art of Akram.

Finally, the applicant has not established the critical nature of a “third metal layer has a thickness of between 2700 and 3300 Angstroms.” “The law is replete with cases in which the difference between the claimed invention and the prior art is some range or other variable within the claims. . . . In such a situation, the applicant must show that the particular range is critical, generally by showing that the claimed range achieves unexpected results relative to the prior art range.” *In re Woodruff*, 919 F.2d 1575, 16 USPQ2d 1934 (Fed. Cir. 1990). Therefore, it would have been obvious to one having ordinary skill in the art at the time the invention was made to have various ranges.

#### ***Response to Arguments***

7. Applicant's arguments filed 11/20/06 have been fully considered but they are not persuasive. First, Applicant argued that “Applicant’s respectfully traverse the Examiner’s opinion that...Yanagida...aids in providing high durability because Yanagida’s device fails to improve the durability of wirebonding.” However, Yanagida discloses that adhesion is increased, which ultimately results in a device that provides high durability (For Example: See Column 3 Lines 17-28 and Column 6 Line 12).

Finally, Applicant argued that “it is believed that the metal layer 20a used for flip-chip mounting method, in Yanagida’s device, is non-analogous to the metal layer 12” used for a wirebonding method, in Akram’s device.” In response to applicant's argument that metal layer

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20a is non-analogous to the metal layer 12''', it has been held that a prior art reference must either be in the field of applicant's endeavor or, if not, then be reasonably pertinent to the particular problem with which the applicant was concerned, in order to be relied upon as a basis for rejection of the claimed invention. See *In re Oetiker*, 977 F.2d 1443, 24 USPQ2d 1443 (Fed. Cir. 1992). In this case, Akram and Yanagida are both from the same field of endeavor, semiconductors.

***Conclusion***

8. **THIS ACTION IS MADE FINAL.** Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the mailing date of this final action.

9. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Monica Lewis whose telephone number is 571-272-1838. If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Zandra Smith can be reached on 571-272-2429. The fax phone number for the organization

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where this application or proceeding is assigned is 571-273-8300 for regular and after final communications.

ML

January 30, 2007

A handwritten signature consisting of the letters "M.L." written in a cursive, flowing script.